



44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748-5089

NTE52

Silicon NPN Transistor

High Voltage, High Speed Switch

Description:

The NTE52 is a silicon NPN transistor in a TO3 type package designed for high voltage, high-speed power switching in inductive circuits where fall time is critical. This device is particularly suited for line-operated switch-mode applications.

Applications:

- Switching Regulators
- Motor Controls
- Inverters
- Solenoid and Relay Drivers

Features:

- Fast Turn-Off Times:
 - 100ns Inductive Fall Time @ +25°C (Typ)
 - 150ns Inductive Crossover Time @ +25°C (Typ)
 - 400ns Inductive Storage Time @ +25°C (Typ)
- Operating Temperature Range: -65° to +200°C

Absolute Maximum Ratings:

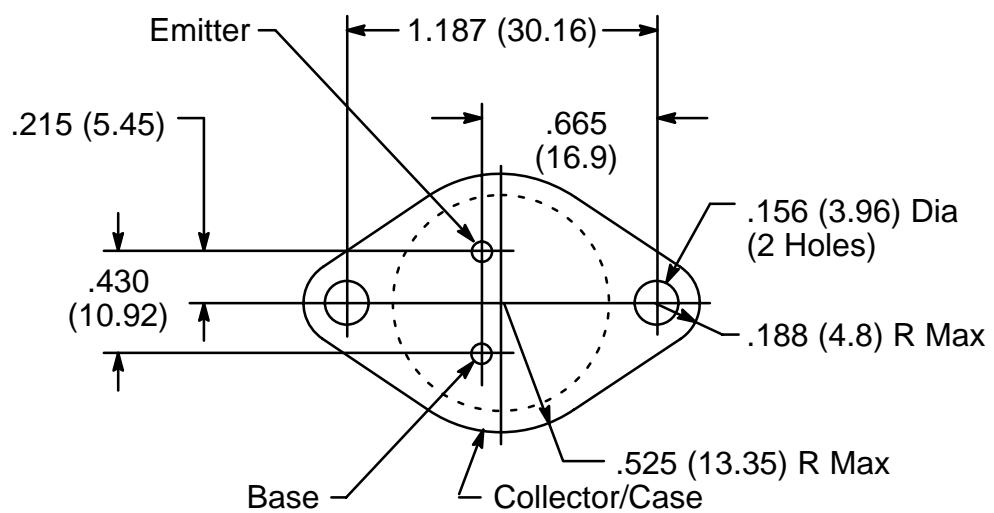
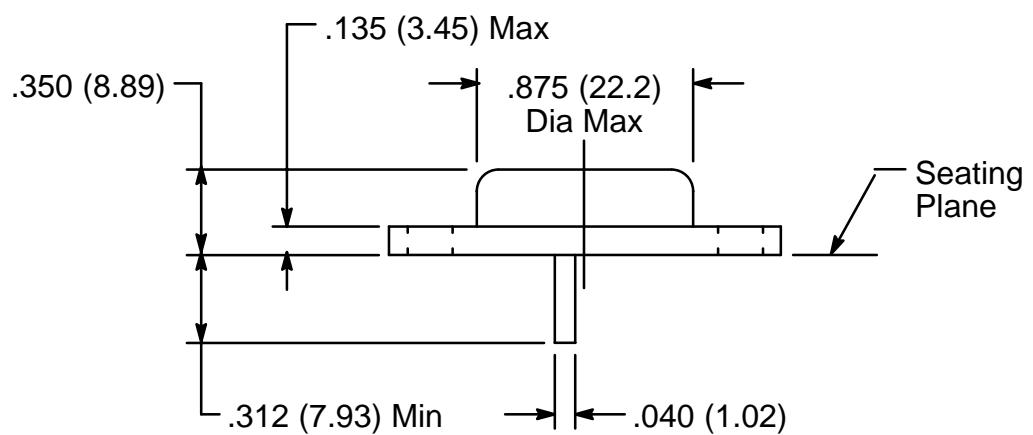
Collector-Emitter Voltage, $V_{CEO(sus)}$	450V
Collector-Emitter Voltage, V_{CEV}	750V
Emitter-Base Voltage, V_{EB}	6V
Collector Current, I_C	
Continuous	5A
Peak (Note 1)	8A
Base Current, I_B	
Continuous	2A
Peak (Note 1)	4A
Total Device Dissipation ($T_C = +25^\circ\text{C}$), P_D	125W
Derate Above 25°C	0.714W/ $^\circ\text{C}$
Total Device Dissipation ($T_C = +100^\circ\text{C}$), P_D	71.5W
Operating Junction Temperatur Range, T_J	-65° to +200°C
Storage Temperatur Range, T_{stg}	-65° to +200°C
Thermal Resistance, Junction-to-Case, R_{thJC}	1.4°C/W
Maximum Lead temperature (During Soldering, 1/8" from case, 5sec), T_L	+275°C

Note 1. Pulse test: Pulse Width = 5ms, Duty Cycle ≤ 10%.

Electrical Characteristics: ($T_C = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF Characteristics (Note 2)						
Collector-Emitter Sustaining Voltage	$V_{CEO(\text{sus})}$	$I_C = 100\text{mA}, I_B = 0$	450	—	—	V
Collector Cutoff Current	I_{CEV}	$V_{CEV} = 750\text{V}, V_{BE(\text{off})} = 1.5\text{V}$	—	—	0.5	mA
		$V_{CEV} = 750\text{V}, V_{BE(\text{off})} = 1.5\text{V}, T_C = +100^\circ\text{C}$	—	—	2.5	mA
	I_{CER}	$V_{CEV} = 750\text{V}, R_{BE} = 50\Omega, T_C = +100^\circ\text{C}$	—	—	3.0	mA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 6\text{V}, I_C = 0$	—	—	1.0	mA
ON Characteristics (Note 2)						
DC Current Gain	h_{FE}	$V_{CE} = 5\text{V}, I_C = 3\text{A}$	8	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(\text{sat})}$	$I_C = 3\text{A}, I_B = 0.6\text{A}$	—	—	1.0	V
		$I_C = 3\text{A}, I_B = 0.6\text{A}, T_C = +100^\circ\text{C}$	—	—	2.0	V
		$I_C = 5\text{A}, I_B = 1\text{A}$	—	—	3.0	V
Base-Emitter Saturation Voltage	$V_{BE(\text{sat})}$	$I_C = 3\text{A}, I_B = 0.6\text{A}$	—	—	1.5	V
		$I_C = 3\text{A}, I_B = 0.6\text{A}, T_C = +100^\circ\text{C}$	—	—	1.5	V
Dynamic Characteristics						
Output Capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{kHz}$	—	—	250	pF
Switching Characteristics (Resistive Load)						
Delay Time	t_d	$V_{CC} = 250\text{V}, I_C = 3\text{A}, I_{B1} = 0.4\text{A}, V_{BE(\text{off})} = 5\text{V}, t_p = 300\mu\text{s}$, Duty Cycle $\leq 2\%$	—	0.03	0.05	μs
Rise Time	t_r		—	0.10	1.40	μs
Storage Time	t_s		—	0.40	0.50	μs
Fall Time	t_f		—	0.175	0.500	μs
Switching Characteristics (Inductive Load, Clamped)						
Storage Time	t_{sv}	$I_C = 3\text{A}$ peak, $V_{clamp} = 250\text{V}, I_{B1} = 0.4\text{A}, V_{BE(\text{off})} = 5\text{V}$	—	0.40	—	μs
Crossover Time	t_c		—	0.15	—	μs
Fall Time	t_{fi}		—	0.10	—	μs
Storage Time	t_{sv}	$I_C = 3\text{A}$ peak, $V_{clamp} = 250\text{V}, I_{B1} = 0.4\text{A}, V_{BE(\text{off})} = 5\text{V}, T_J = +100^\circ\text{C}$	—	0.70	2.0	μs
Crossover Time	t_c		—	0.28	0.50	μs
Fall Time	t_{fi}		—	0.15	0.30	μs

Note 2. Pulse test: Pulse Width = $300\mu\text{s}$, Duty Cycle $\leq 2\%$.



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by NTE manufacturer:

Other Similar products are found below :

[619691C](#) [MCH4017-TL-H](#) [MJ15024/WS](#) [MJ15025/WS](#) [BC546/116](#) [BC556/FSC](#) [BC557/116](#) [BSW67A](#) [HN7G01FU-A\(T5L,F,T](#)
[NJVMJD148T4G](#) [NSVMMBT6520LT1G](#) [NTE187A](#) [NTE195A](#) [NTE2302](#) [NTE2330](#) [NTE2353](#) [NTE316](#) [IMX9T110](#) [NTE63](#) [NTE65](#)
[C4460](#) [SBC846BLT3G](#) [2SA1419T-TD-H](#) [2SA1721-O\(TE85L,F\)](#) [2SA1727TLP](#) [2SA2126-E](#) [2SB1202T-TL-E](#) [2SB1204S-TL-E](#) [2SC5488A-TL-H](#)
[2SD2150T100R](#) [SP000011176](#) [FMC5AT148](#) [2N2369ADCSM](#) [2SB1202S-TL-E](#) [2SC2412KT146S](#) [2SC4618TLN](#) [2SC5490A-TL-H](#)
[2SD1816S-TL-E](#) [2SD1816T-TL-E](#) [CMXT2207 TR](#) [CPH6501-TL-E](#) [MCH4021-TL-E](#) [BC557B](#) [TTC012\(Q\)](#) [BULD128DT4](#) [JANTX2N3810](#)
[Jantx2N5416](#) [US6T6TR](#) [KSF350](#) [068071B](#)